

SN54LS222, SN54LS224, SN54LS227, SN54LS228 SN74LS222, SN74LS224, SN74LS227, SN74LS228 16 X 4 SYNCHRONOUS FIRST-IN FIRST-OUT MEMORIES

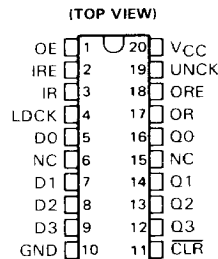
JANUARY 1981 REVISED MARCH 1985

- Independent Synchronous Inputs and Outputs
- 16 Words of 4 Bits Each
- 3-State Outputs Drive Bus Lines Directly
- Data Rates from 0 to 10 MHz
- Fall-Through Time . . . 50 ns Typ
- Data Terminals Arranged for Optimum PC Board Layout
- Expandable Using External Gating

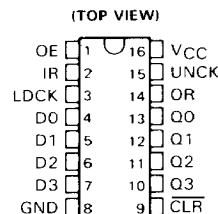
description

These 64-bit memories are Low-Power Schottky memory arrays organized as 16 words of 4 bits each. They can be expanded in multiples of $15m + 1$ words or $4n$ bits, or both, (where n is the number of packages in the vertical array and m is the number of packages in the horizontal array) however some external gating is required (see Figure 1). For longer words using the 'LS224 or 'LS228 the IR signals of the first-rank packages and OR signals of the last-rank packages must be ANDed for proper synchronization.

SN54LS222, SN54LS227 . . . J PACKAGE
SN74LS222, SN74LS227 . . . J OR N PACKAGE



SN54LS224, SN54LS228 . . . J PACKAGE
SN74LS224, SN74LS228 . . . J OR N PACKAGE



NC No internal connection

For chip carrier information
contact the factory.

TYPE	INPUT-READY ENABLE AND OUTPUT READY ENABLE	OUTPUT
'LS222	Yes	3-State
'LS224	No	3-State
'LS227	Yes	Open-collector
'LS228	No	Open-collector

operation

A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. These FIFOs are designed to process data at rates from 0 to 10 MHz in a bit-parallel format, word by word. Data is written into the memory on a high-to-low transition at the load clock input (LDCK) and read out on a low-to-high transition at the unload clock input (UNCK).

The memory is full when the number of words clocked in exceeds the number of words clocked out by 16. When the memory is full, LDCK signals have no effect. When the memory is empty, UNCK signals have no effect.

Status of the FIFO memory (see timing diagram) is monitored by the input ready (IR) and output ready (OR) flags that indicate "not full" and "not empty" conditions. The IR output will be high only when the memory is not full and the LDCK input is low. The OR output will be high only when the memory is not empty and UNCK is high.

A low level at the clear ($\overline{\text{CLR}}$) input resets the internal stack control counters and also sets IR high and OR low to indicate that old data remaining at the data outputs is invalid. Data outputs are noninverting with respect to the data inputs and are at high impedance when output enable (OE) is low. OE does not affect the IR and OR outputs.

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

TEXAS
INSTRUMENTS

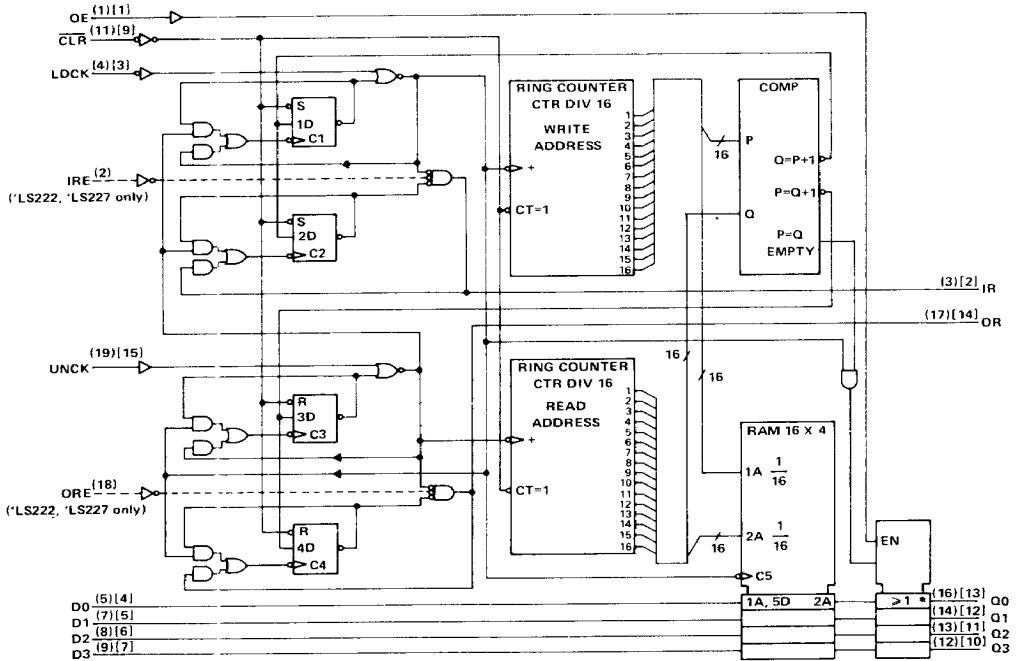
POST OFFICE BOX 225012 • DALLAS, TEXAS 75265

Copyright © 1979, Texas Instruments Incorporated

2
LSI Devices

SN54LS222, SN54LS224, SN54LS227, SN54LS228
SN74LS222, SN74LS224, SN74LS227, SN74LS228
16 X 4 SYNCHRONOUS FIRST-IN FIRST-OUT MEMORIES

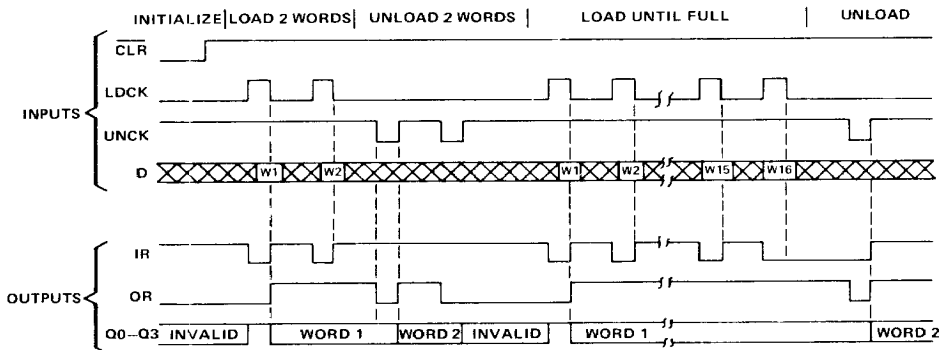
functional block diagram (positive logic)



*LS222 and LS224 have 3 state (◊) outputs.
 *LS227 and LS228 have open-collector (◊) outputs.

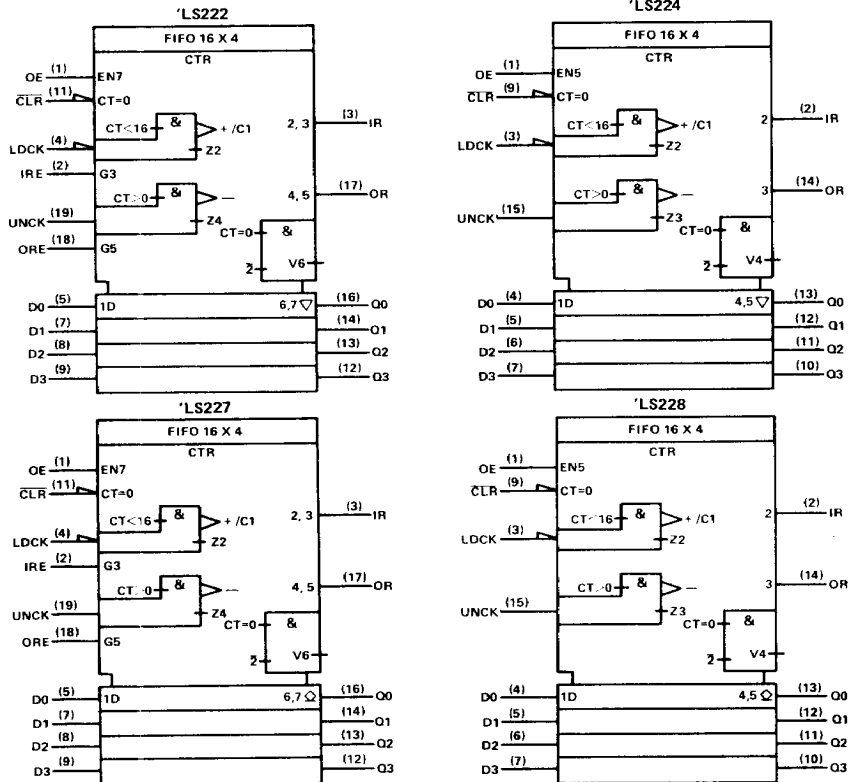
[LS222 and LS227 pin numbers]
 [LS224 and LS228 pin numbers]

timing diagram



**SN54LS222, SN54LS224, SN54LS227, SN54LS228
SN74LS222, SN74LS224, SN74LS227, SN74LS228
16 X 4 SYNCHRONOUS FIRST-IN FIRST-OUT MEMORIES**

logic symbols†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

These symbols are functionally accurate but do not show the details of implementation; for these, see the functional block diagram. The symbol represents the memory as if it were controlled by a single counter whose content is the number of words stored at that time. Output data is invalid when the counter content is 0.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V_{CC} (See Note 1)	7 V
Input voltage	7 V
Off-state output voltage	5.5 V
Operating free-air temperature range:	
SN54LS222, SN54LS224, SN54LS227, SN54LS228	-55 °C to 125 °C
SN74LS222, SN74LS224, SN74LS227, SN74LS228	0 °C to 70 °C
Storage temperature range	-65 °C to 150 °C

NOTE 1: Voltage values are with respect to network ground terminal.

SN54LS222, SN54LS224, SN74LS222, SN74LS224
16 X 4 SYNCHRONOUS FIRST-IN FIRST-OUT MEMORIES
WITH 3-STATE OUTPUTS

recommended operating conditions

			SN54LS ¹			SN74LS ¹			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	
V _{CC}	Supply voltage		4.5	5	5.5	4.75	5	5.25	V
V _{IH}	High-level input voltage		2			2			V
V _{IL}	Low-level input voltage				0.7			0.8	V
I _{OH}	High-level output current	Q			-1			-2.6	mA
		IR, OR			-0.4			-0.4	
I _{OL}	Low-level output current	Q			12			24	mA
		IR, OR			4			8	
t _w	Pulse duration	LDCK high	60			60			ns
		LDCK low	15			15			
		UNCK low	30			30			
		UNCK high	30			30			
		CLR low	20			20			
t _{su}	Setup time	D to LDCK↓	50			50			ns
		LDCK↓ before UNCK↓	50			50			
		UNCK↑ before LDCK↑	50			50			
t _h	Hold time	D from LDCK↓	0			0			ns
T _A	Operating free-air temperature		-55		125	0		70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS [†]				SN54LS ¹			SN74LS ¹			UNIT
						MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
V _{IK}		V _{CC} = MIN, I _I = -18 mA						-1.5			-1.5	V
V _{OH}	Q	V _{CC} = MIN, I _{OH} = MAX				2.4	3.3		2.4	3.4		V
	IR, OR	V _{CC} = MIN, I _{OH} = -0.4 mA				2.5	3.4		2.7	3.4		
V _{OL}	Q	V _{CC} = MIN, I _{OL} = 12 mA					0.25	0.4		0.25	0.4	V
		V _{CC} = MIN, I _{OL} = 24 mA								0.35	0.5	
	IR, OR	V _{CC} = MIN, I _{OL} = 4 mA					0.25	0.4		0.25	0.4	
		V _{CC} = MIN, I _{OL} = 8 mA								0.35	0.5	
I _{OZH}	Q	V _{CC} = MAX, V _O = 2.7 V						20			20	μA
I _{OZL}	Q	V _{CC} = MAX, V _O = 0.4 V						-20			-20	μA
I _I		V _{CC} = MAX, V _I = 7 V						0.1			0.1	mA
I _{IH}		V _{CC} = MAX, V _I = 2.7 V						20			20	μA
I _{IL}		V _{CC} = MAX, V _I = 0.4 V						-0.4			-0.4	mA
I _{OS} [§]	Q	V _{CC} = MAX,				-30		-130	-30		-130	mA
	IR, OR					-20		-100	-20		-100	
I _{CC}		V _{CC} = MAX,	Outputs high			84	135		84	135		mA
			Outputs low			87	155		87	155		
			Outputs disabled			89	155		89	155		

[†]For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

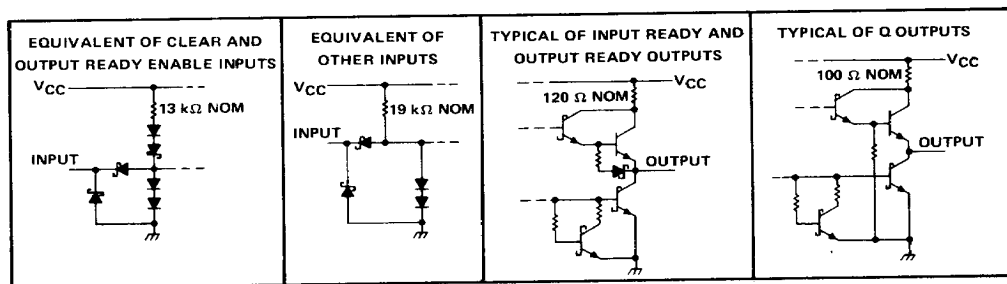
[‡]All typical values are at V_{CC} = 5 V, T_A = 25°C.

[§]Not more than one output should be shorted at a time, and duration of the short-circuit should not exceed one second.

LSI Devices

PARAMETER	FROM	TO	TEST CONDITIONS	'LS222			'LS224			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
t _{PLH}	IRE↑	IR	R _L = 2 kΩ, C _L = 15 pF, See Note 2		23	35				ns
t _{PHL}	IRE↓	IR			9	15				ns
t _{PLH}	ORE↑	OR			22	35				ns
t _{PHL}	ORE↓	OR			9	15				ns
t _{PLH}	LDCK↑	IR			25	40	25	40		ns
t _{PHL}	LDCK↓	IR			36	50	36	50		ns
t _{PLH}	LDCK↑	OR			48	70	48	70		ns
t _{PHL}	LDCK↓	OR			29	45	29	45		ns
t _{PLH}	UNCK↑	OR			28	45	28	45		ns
t _{PHL}	UNCK↓	OR			49	70	49	70		ns
t _{PLH}	UNCK↑	IR			36	55	36	55		ns
t _{PHL}	UNCK↓	IR			25	40	25	40		ns
t _{PLH}	CLR↑	IR	R _L = 667 Ω, C _L = 45 pF, See Note 2		34	50	34	50		ns
t _{PHL}	CLR↓	OR			54	80	54	80		ns
t _{PLH}	LDCK↑	Q			45	70	45	70		ns
t _{PHL}	LDCK↓	Q			22	35	22	35		ns
t _{PZL}	OE↑	Q			21	35	21	35		ns
t _{PZH}	OE↓	Q			16	30	16	30		ns
t _{PLZ}	OE↑	Q	R _L = 667 Ω, C _L = 5 pF, See Note 2		18	30	18	30		ns
t _{PHZ}	OE↓	Q								

schematics of inputs and outputs



SN54LS227, SN54LS228, SN74LS227, SN74LS228 **16 X 4 SYNCHRONOUS FIRST-IN FIRST-OUT MEMORIES** **WITH OPEN-COLLECTOR OUTPUTS**

recommended operating conditions

			SN54LS*			SN74LS*			UNIT	
			MIN	NOM	MAX	MIN	NOM	MAX		
V _{CC}	Supply voltage		4.5	5	5.5	4.75	5	5.25	V	
V _{IH}	High-level input voltage		2			2			V	
V _{IL}	Low-level input voltage				0.7			0.8	V	
V _{OH}	High-level output voltage	Q			5.5			5.5	V	
I _{OH}	High-level output current	IR, OR			-0.4			-0.4	mA	
I _{OL}	Low-level output current	Q			12			24		
		IR, OR			4			8		
t _w	Pulse duration	LDCK high			60			60	ns	
		LDCK low			15			15		
		UNCK low			30			30		
		UNCK high			30			30		
		CLR low			20			20		
t _{su}	Setup time	D to LDCK↓			50			50	ns	
		LDCK, before UNCK↓			50			50		
		UNCK↑ before LDCK↑			50			50		
t _h	Hold time	D from LDCK↓			0			0	ns	
T _A	Operating free-air temperature				-55		125	0	70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS†	SN54LS [*]			SN74LS [*]			UNIT
			MIN	TYP‡	MAX	MIN	TYP‡	MAX	
V _{IK}		V _{CC} = MIN, I _I = -18 mA			-1.5			-1.5	V
I _{OH}	Q	V _{CC} = MIN, V _{OH} = 5.5 V			0.1			0.1	mA
V _{OH}	IR, OR	V _{CC} = MIN, I _{OH} = -0.4 mA	2.5	3.4		2.7	3.4		V
V _{OL}	Q	V _{CC} = MIN, I _{OL} = 12 mA		0.25	0.4		0.25	0.4	V
		V _{CC} = MIN, I _{OL} = 24 mA					0.35	0.5	
	IR, OR	V _{CC} = MIN, I _{OL} = 4 mA		0.25	0.4		0.25	0.4	
		V _{CC} = MIN, I _{OL} = 8 mA					0.35	0.5	
I _{OZH}	Q	V _{CC} = MAX, V _O = 2.7 V			20			20	μA
I _{OZL}	Q	V _{CC} = MAX, V _O = 0.4 V			-20			-20	μA
I _I		V _{CC} = MAX, V _I = 7 V			0.1			0.1	mA
I _{IH}		V _{CC} = MAX, V _I = 2.7 V			20			20	μA
I _{IL}		V _{CC} = MAX, V _I = 0.4 V			-0.4			-0.4	mA
I _{OS} §	IR, OR	V _{CC} = MAX	-20		-100	-20		-100	mA
I _{CC}	V _{CC} = MAX	Outputs high		84	135		84	135	mA
		Outputs low		87	155		87	155	
		Outputs disabled		89	155		89	155	

†For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

‡All typical values are at V_{CC} = 5 V, T_A = 25°C.

§Not more than one output should be shorted at a time, and duration of the short-circuit should not exceed one second.

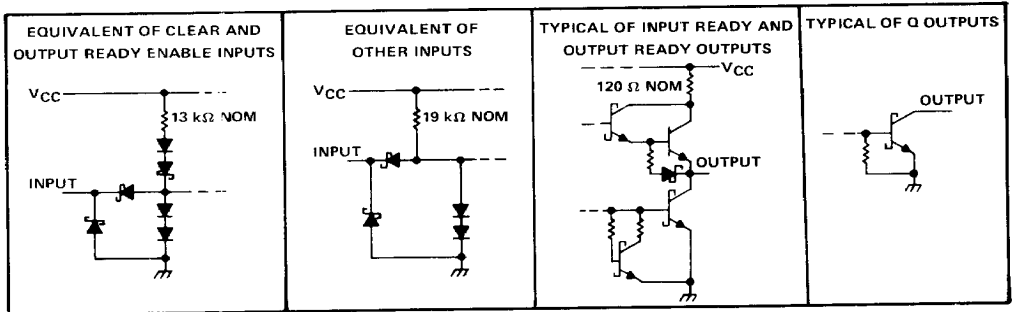
SN54LS227, SN54LS228, SN74LS227, SN74LS228 **16 X 4 SYNCHRONOUS FIRST-IN FIRST-OUT MEMORIES** **WITH OPEN-COLLECTOR OUTPUTS**

switching characteristics, $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER	FROM	TO	TEST CONDITIONS	'LS227			'LS228			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	IRE*	IR	$R_L = 2\text{ k}\Omega$, $C_L = 15\text{ pF}$, See Note 2	23		35				ns
t_{PHL}	IRE.	IR			9	15				ns
t_{PLH}	ORE*	OR		22		35				ns
t_{PHL}	ORE.	OR			9	15				ns
t_{PLH}	LDCK*	IR		25		40	25		40	ns
t_{PHL}	LDCK.	IR			36	50	36		50	ns
t_{PLH}	LDCK*	OR		48		70	48		70	ns
t_{PHL}	LDCK.	OR			29	45	29		45	ns
t_{PLH}	UNCK*	OR		28		45	28		45	ns
t_{PHL}	UNCK.	OR			49	70	49		70	ns
t_{PLH}	UNCK*	IR		36		55	36		55	ns
t_{PHL}	UNCK.	IR			25	40	25		40	ns
t_{PLH}	CLR.	IR	$R_L = 667\ \Omega$, $C_L = 45\text{ pF}$, See Note 2	34		50	34		50	ns
t_{PHL}	CLR.	OR			54	80	54		80	ns
t_{PLH}	LDCK*	Q		45		70	45		70	ns
t_{PHL}	LDCK.	Q			21	30	21		30	ns
t_{PLH}	OE*	Q		20		35	20		35	ns
t_{PHL}	OE.	Q								ns

NOTE 2: Load circuits and voltage waveforms are shown in Section 1.

schematics of inputs and outputs



LSI Devices 2



2-20